

SBR20150CT-prel SBR20150CTI-prel SBR20150CTB-prel

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units	
I _{F(AV)} Rectangular Waveform	20	Α	
V_{RRM}	150	V	
I _R @150V, Tj=25°C	12	nA, typ	
Tj(operating/storage)	-65 to 200	°C	

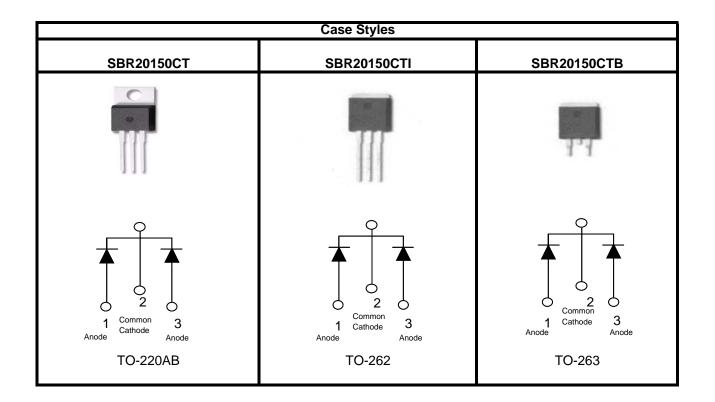
Device optimized for high temperature Power Supply applications

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263 packages

ELECTRICAL:

- * Ultra High Thermal Reliability
- * Low Reverse Leakage
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 200°C Operating Junction Temperature



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(at 25°C unless otherwise specified)	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V _{RM} V _{RWM} V _{RRM}	150		Volts
RMS Reverse Voltage	$V_{R(RMS)}$	150		Volts
Average Rectified Forward Current (Rated V _R -20Khz Square Wave)-50% duty cycle	Io	20		Amps
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	180		Amps
Peak Repetitive Reverse Surge Current (2uS-2Khz)	I _{RRM}	3		Amps
Instantaneous Forward Voltage (per leg) $I_F = 10A$; $T_J = 25^{\circ}C$ $I_F = 20A$; $T_J = 25^{\circ}C$ $I_F = 10A$; $T_J = 125^{\circ}C$	V _F	Typ 0.82 0.94 0.67	Max 0.86 0.98 0.71	Volts
Maximum Instantaneous Reverse Current at Rated V_{RM} $T_{\text{J}} = 25^{\circ}\text{C}$ $T_{\text{J}} = 125^{\circ}\text{C}$	I _R .	Тур 0.012 0.09	Max 5 1	uA mA
Maximum Rate of Voltage Change (at Rated V _R)	dv/dt	10,000		V/uS
Maximum Thermal Resistance JC	$R\theta_{JC}$	2		°C/W
Operating and Storage Junction Temperature	T_J	-65 to +200		°C

NOTE: Dice are available for customer applications.

^{*} Pulse width < 300 uS, Duty cycle < 2%

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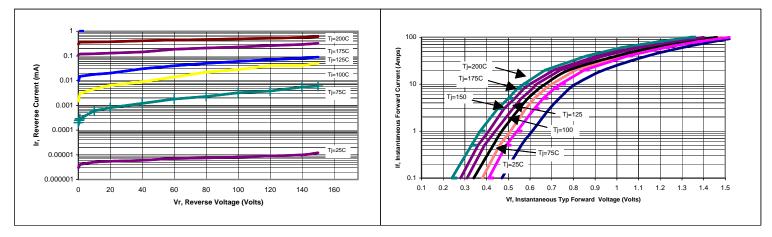


Figure 1: Typical Reverse Current

Figure 2: Typical Forward Voltage

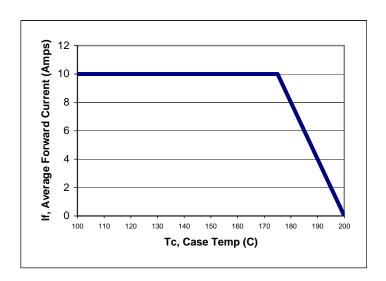


Figure 3: Current Derating, Case

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